

Hyeong Joon Kim

List of Publications by Year in descending order

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191
papers

4,073
citations

101384

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3797
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#	ARTICLE	IF	CITATIONS
1	Infrared spectroscopy study of low-dielectric-constant fluorine-incorporated and carbon-incorporated silicon oxide films. <i>Journal of Applied Physics</i> , 2001, 90, 3367-3370.	1.1	154
2	Low-k SiO ₂ -C composite films prepared by plasma-enhanced chemical vapor deposition using bis-trimethylsilylmethane precursor. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2000, 18, 1216-1219.	0.9	123
3	Dielectric and electrical properties of sputter grown (Ba,Sr)TiO ₃ thin films. <i>Journal of Applied Physics</i> , 1999, 86, 506-513.	1.1	122
4	Current conduction mechanisms in atomic-layer-deposited HfO ₂ /nitrided SiO ₂ stacked gate on 4H silicon carbide. <i>Journal of Applied Physics</i> , 2008, 103, .	1.1	121
5	Deposition of ZnO thin films by magnetron sputtering for a film bulk acoustic resonator. <i>Thin Solid Films</i> , 2003, 435, 179-185.	0.8	107
6	Origin of low dielectric constant of carbon-incorporated silicon oxide film deposited by plasma enhanced chemical vapor deposition. <i>Journal of Applied Physics</i> , 2001, 90, 2469-2473.	1.1	101
7	Microstructural evolution and preferred orientation change of radio frequency magnetron sputtered ZnO thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1996, 14, 1943-1948.	0.9	80
8	Epitaxial growth of ZnO thin films on R-plane sapphire substrate by radio frequency magnetron sputtering. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1997, 15, 1103-1107.	0.9	79
9	Improvement of the photo-bias stability of the ZnSnO field effect transistors by an ozone treatment. <i>Journal of Materials Chemistry</i> , 2012, 22, 10994.	6.7	76
10	Effects of surface roughness of substrates on the c-axis preferred orientation of ZnO films deposited by r.f. magnetron sputtering. <i>Thin Solid Films</i> , 2003, 423, 262-266.	0.8	66
11	Leakage current of sol-gel derived Pb(Zr,Ti)O ₃ thin films having Pt electrodes. <i>Applied Physics Letters</i> , 1999, 75, 3411-3413.	1.5	63
12	High-Quality Low-Temperature Silicon Oxide by Plasma-Enhanced Atomic Layer Deposition Using a Metal-Organic Silicon Precursor and Oxygen Radical. <i>IEEE Electron Device Letters</i> , 2010, 31, 857-859.	2.2	63
13	Photobias Instability of High Performance Solution Processed Amorphous Zinc Tin Oxide Transistors. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 3255-3261.	4.0	61
14	Characterization of low-dielectric-constant SiOC thin films deposited by PECVD for interlayer dielectrics of multilevel interconnection. <i>Surface and Coatings Technology</i> , 2003, 171, 39-45.	2.2	59
15	Role of ZrO ₂ incorporation in the suppression of negative bias illumination-induced instability in ZnSnO thin film transistors. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	59
16	Deposition and characterization of ZrO ₂ thin films on silicon substrate by MOCVD. <i>Journal of Materials Research</i> , 1993, 8, 1361-1367.	1.2	57
17	Thermodynamic Calculations and Metallorganic Chemical Vapor Deposition of Ruthenium Thin Films Using Bis(ethyl- η -cyclopentadienyl)Ru for Memory Applications. <i>Journal of the Electrochemical Society</i> , 2000, 147, 1161.	1.3	55
18	Epitaxial growth of CoSi ₂ layer on (100)Si and facet formation at the CoSi ₂ /Si interface. <i>Journal of Applied Physics</i> , 1995, 78, 1725-1730.	1.1	53

#	ARTICLE	IF	CITATIONS
19	Thickness dependence of microstructural evolution of ZnO films deposited by rf magnetron sputtering. Journal of Materials Research, 1998, 13, 1260-1265.	1.2	52
20	Preparation of high quality RuO ₂ electrodes for high dielectric thin films by low pressure metal organic chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 2768-2771.	0.9	52
21	Improvement in Photo-Bias Stability of High-Mobility Indium Zinc Oxide Thin-Film Transistors by Oxygen High-Pressure Annealing. IEEE Electron Device Letters, 2013, 34, 894-896.	2.2	52
22	Influence of Substrates on the Nucleation and Growth Behaviors of Ge ₂ Sb ₂ Te ₅ Films by Combined Plasma-Enhanced Atomic Layer and Chemical Vapor Deposition. Chemistry of Materials, 2009, 21, 2386-2396.	3.2	51
23	Properties of lanthanum oxide thin films deposited by cyclic chemical vapor deposition using tris(isopropyl-cyclopentadienyl)lanthanum precursor. Journal of Applied Physics, 2006, 100, 024111.	1.1	50
24	Hydration of r.f. magnetron sputtered MgO thin films for a protective layer in AC plasma display panel. Thin Solid Films, 2003, 435, 95-101.	0.8	49
25	Metal-Core Printed Circuit Board With Alumina Layer by Aerosol Deposition Process. IEEE Electron Device Letters, 2008, 29, 991-993.	2.2	48
26	SiO ₂ Incorporation Effects in Ge ₂ Sb ₂ Te ₅ Films Prepared by Magnetron Sputtering for Phase Change Random Access Memory Devices. Electrochemical and Solid-State Letters, 2006, 9, G259.	2.2	46
27	Plasma-Enhanced Atomic Layer Deposition of TiO ₂ and Al-Doped TiO ₂ Films Using N ₂ O and O ₂ Reactants. Journal of the Electrochemical Society, 2009, 156, G138.	1.3	46
28	Improvements in Growth Behavior of CVD Ru Films on Film Substrates for Memory Capacitor Integration. Journal of the Electrochemical Society, 2005, 152, C15.	1.3	44
29	Threshold switching in Si-As-Te thin film for the selector device of crossbar resistive memory. Applied Physics Letters, 2012, 100, .	1.5	44
30	Effect of oblique sputtering on microstructural modification of ZnO thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1997, 15, 1194-1199.	0.9	42
31	Phase transformation behaviors of SiO ₂ doped Ge ₂ Sb ₂ Te ₅ films for application in phase change random access memory. Applied Physics Letters, 2008, 92, .	1.5	42
32	Impact of the Cation Composition on the Electrical Performance of Solution-Processed Zinc Tin Oxide Thin-Film Transistors. ACS Applied Materials & Interfaces, 2014, 6, 14026-14036.	4.0	42
33	Fabrication and characterization of 4H-SiC planar MESFETs. Microelectronic Engineering, 2006, 83, 160-164.	1.1	41
34	Effect of selenization pressure on CuInSe ₂ thin films selenized using co-sputtered Cu-In precursors. Solar Energy Materials and Solar Cells, 2000, 62, 357-368.	3.0	40
35	Electronic Properties of Atomic-Layer-Deposited Al ₂ O ₃ /Thermal-Nitrided SiO ₂ Stacking Dielectric on 4H SiC. Electrochemical and Solid-State Letters, 2007, 10, H69.	2.2	39
36	Improved Electronic Performance of $\text{HfO}_2/\text{SiO}_2$ Stacking Gate Dielectric on 4H SiC. IEEE Transactions on Electron Devices, 2007, 54, 3409-3413.	1.6	38

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37	Anomalous behavior of negative bias illumination stress instability in an indium zinc oxide transistor: A cation combinatorial approach. Applied Physics Letters, 2012, 101, 092107.	1.5	38
38	Hydration behavior of MgO single crystals and thin films. Journal of Materials Research, 2003, 18, 2895-2903.	1.2	36
39	Analysis of current conduction mechanisms in atomic-layer-deposited Al ₂ O ₃ gate on 4H silicon carbide. Applied Physics Letters, 2007, 90, 162113.	1.5	36
40	Preparation of carbon nanotubes by DC arc discharge process under reduced pressure in an air atmosphere. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 133, 241-244.	1.7	35
41	Effects of ZrO ₂ doping on HfO ₂ resistive switching memory characteristics. Applied Physics Letters, 2014, 105, .	1.5	35
42	SiO ₂ -doped Ge ₂ Sb ₂ Te ₅ thin films with high thermal efficiency for applications in phase change random access memory. Nanotechnology, 2011, 22, 254005.	1.3	34
43	Cation Composition Control of MOCVD (Ba,Sr)TiO ₃ Thin Films along the Capacitor Hole. Journal of the Electrochemical Society, 2002, 149, C585.	1.3	33
44	Property Changes of Aluminum Oxide Thin Films Deposited by Atomic Layer Deposition under Photon Radiation. Journal of the Electrochemical Society, 2006, 153, F87.	1.3	32
45	Properties of Aluminum Nitride Thin Films Deposited by an Alternate Injection of Trimethylaluminum and Ammonia under Ultraviolet Radiation. Journal of the Electrochemical Society, 2006, 153, C229.	1.3	31
46	The effect of substrate temperature on the composition and growth of tantalum oxide thin films deposited by plasma-enhanced chemical vapour deposition. Thin Solid Films, 1991, 206, 102-106.	0.8	30
47	Metallorganic Chemical Vapor Deposition of Ru Films Using Cyclopentadienyl-Propylcyclopentadienylruthenium(II) and Oxygen. Journal of the Electrochemical Society, 2002, 149, C317.	1.3	30
48	The protection of MgO film against hydration by using Al ₂ O ₃ capping layer deposited by magnetron sputtering method. Thin Solid Films, 2003, 435, 199-204.	0.8	30
49	Nitrogen incorporation engineering and electrical properties of high-k gate dielectric (HfO ₂) _{Tj} ETQq1 1 0.784314 rgBT /Overlo Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1838.	1.6	29
50	Investigation of interface trap states in TiN/Al ₂ O ₃ /p-Si capacitor by deep level transient spectroscopy. Applied Physics Letters, 2003, 82, 1066-1068.	1.5	28
51	Effects of post-oxidation annealing temperature on ZrO ₂ thin film deposited on 4H-SiC substrate. Materials Science in Semiconductor Processing, 2011, 14, 13-17.	1.9	27
52	Growth and electrical properties of silicon oxide grown by atomic layer deposition using Bis(ethyl-methyl-amino)silane and ozone. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	0.9	27
53	The Role of the Methyl and Hydroxyl Groups of Low-k Dielectric Films on the Nucleation of Ruthenium by ALD. Electrochemical and Solid-State Letters, 2008, 11, H210.	2.2	26
54	Improving the Morphological and Optical Properties of Sputtered Indium Tin Oxide Thin Films by Adopting Ultralow-Pressure Sputtering. Journal of the Electrochemical Society, 2009, 156, J6.	1.3	26

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55	The Formation of an Almost Full Atomic Monolayer via Surface Modification by N ₂ -O-Plasma in Atomic Layer Deposition of ZrO ₂ Thin Films. Chemistry of Materials, 2009, 21, 4374-4379.	3.2	26
56	Ti-electrode effects of NiO based resistive switching memory with Ni insertion layer. Applied Physics Letters, 2012, 100, .	1.5	26
57	The preparation of carbon nanotubes by dc arc discharge using a carbon cathode coated with catalyst. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 130, 73-80.	1.7	25
58	The structures of low dielectric constant SiOC thin films prepared by direct and remote plasma enhanced chemical vapor deposition. Thin Solid Films, 2007, 515, 5035-5039.	0.8	25
59	Improvement of dielectric properties of (Ba,Sr)TiO ₃ thin films deposited by pulse injection chemical vapor deposition. Applied Physics Letters, 1998, 72, 786-788.	1.5	23
60	Electrical Properties of the La ₂ O ₃ /4H-SiC Interface Prepared by Atomic Layer Deposition Using La(iPrCp) ₃ and H ₂ O. Materials Science Forum, 2006, 527-529, 1083-1086.	0.3	23
61	Effect of O ₂ Addition on the Deposition of Pt Thin Films by Metallorganic Chemical Vapor Deposition. Journal of the Electrochemical Society, 1998, 145, 1066-1069.	1.3	22
62	The Effect of the Dehydration of MgO Films on their XPS Spectra and Electrical Properties. Journal of the Electrochemical Society, 2007, 154, J408.	1.3	22
63	Electrical conduction properties of sputter-grown (Ba,Sr)TiO ₃ thin films having IrO ₂ electrodes. Applied Physics Letters, 2000, 76, 1609-1611.	1.5	21
64	Enhanced Nucleation Behavior of Atomic-Layer-Deposited Ru Film on Low-k Dielectrics Afforded by UV-O ₃ Treatment. Electrochemical and Solid-State Letters, 2008, 11, G5.	2.2	21
65	Substrate Dependent Growth Rate of Plasma-Enhanced Atomic Layer Deposition of Titanium Oxide Using N ₂ O Gas. Electrochemical and Solid-State Letters, 2010, 13, G13.	2.2	21
66	Composition-dependent structural and electrical properties of p-type SnO _x thin films prepared by reactive DC magnetron sputtering: effects of oxygen pressure and heat treatment. RSC Advances, 2016, 6, 71757-71766.	1.7	21
67	Stress measurements of radio-frequency reactively sputtered RuO ₂ thin films. Journal of Applied Physics, 1996, 80, 822-826.	1.1	20
68	Effect of Catalyst Layer Density and Growth Temperature in Rapid Atomic Layer Deposition of Silica Using Tris(<i>tert</i> -pentoxy)silanol. ACS Applied Materials & Interfaces, 2011, 3, 1633-1639.	4.0	20
69	Comparison of thermal and atomic-layer-deposited oxides on 4H-SiC after post-oxidation-annealing in nitric oxide. Applied Physics Letters, 2012, 100, .	1.5	20
70	Epitaxial growth of CoSi ₂ on Si wafer using Co/Ta bilayer. Journal of Applied Physics, 1993, 74, 3156-3161.	1.1	19
71	Improvement in the Crystalline Quality of Epitaxial GaN Films Grown by MOCVD by Adopting Porous 4H-SiC Substrate. Electrochemical and Solid-State Letters, 2004, 7, C43.	2.2	19
72	Thermal Annealing Effects on the Atomic Layer Deposited LaAlO ₃ Thin Films on Si Substrate. Electrochemical and Solid-State Letters, 2008, 11, G33.	2.2	19

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73	Heteroepitaxial growth of 4H-SiC thin films on Si(100) substrate using bis(trimethylsilyl)methane. Applied Physics Letters, 1996, 69, 4053-4055.	1.5	18
74	Relationship between the microstructure and the discharge characteristics of MgO protecting layer in alternating current plasma display panels. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 1162-1166.	0.9	18
75	Homoepitaxial growth and electrical characterization of iron-doped semi-insulating 4H-SiC epilayer. Applied Physics Letters, 2006, 89, 152112.	1.5	18
76	Deposition Characteristics and Annealing Effect of La_2O_3 Films Prepared Using $\text{La}(\text{iPrCp})_3$ Precursor. Journal of the Electrochemical Society, 2007, 154, G49.	1.3	18
77	Dependence of ferroelectric performance of sol-gel-derived $\text{Pb}(\text{Zr,Ti})\text{O}_3$ thin films on bottom-Pt-electrode thickness. Applied Physics Letters, 2002, 81, 3224-3226.	1.5	17
78	Buffer-layer-free growth of high-quality epitaxial GaN films on 4H-SiC substrate by metal-organic chemical vapor deposition. Journal of Crystal Growth, 2005, 276, 407-414.	0.7	17
79	Improved Nucleation Behavior of Ru Thin Films Prepared by MOCVD on TiCl_4 Pretreated Substrates. Electrochemical and Solid-State Letters, 2007, 10, D113.	2.2	17
80	Layer Reversal of Co/Zr Bilayer and Epitaxial Growth of CoSi_2 Layer on Si(001) Substrate. Journal of the Electrochemical Society, 1995, 142, 2805-2812.	1.3	16
81	Improvements in electrical properties of $(\text{Ba,Sr})\text{TiO}_3$ capacitor with chemical vapor deposited Pt top electrode using Pt hexafluoroacetylacetonate. Applied Physics Letters, 1999, 74, 3489-3491.	1.5	16
82	The reason for the increased threshold switching voltage of SiO_2 doped $\text{Ge}_2\text{Sb}_2\text{Te}_5$ thin films for phase change random access memory. Applied Physics Letters, 2009, 95, 112110.	1.5	16
83	Comprehensive Studies on the Carrier Transporting Property and Photo-Bias Instability of Sputtered Zinc Tin Oxide Thin Film Transistors. IEEE Transactions on Electron Devices, 2014, 61, 3191-3198.	1.6	16
84	Investigation into the Structural and Electrical Properties of a-SiCO:H as a Diffusion Barrier to Copper. Journal of the Electrochemical Society, 2006, 153, F228.	1.3	15
85	Dependency of threshold switching on density of localized states of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ thin films for phase change random access memory. Applied Physics Letters, 2008, 93, 172114.	1.5	15
86	Effect of Postoxidation Annealing on High Temperature Grown $\text{SiO}_2/\text{4H-SiC}$ Interfaces. Journal of the Electrochemical Society, 2010, 157, H196.	1.3	15
87	Improving the Barrier Height Uniformity of 4H-SiC Schottky Barrier Diodes by Nitric Oxide Post-Oxidation Annealing. IEEE Electron Device Letters, 2014, 35, 868-870.	2.2	15
88	Preferred orientation and microstructure of Ni-Zn-Cu ferrite thin films deposited by rf magnetron sputtering. Journal of Materials Research, 1994, 9, 2425-2433.	1.2	13
89	The effects of substrate and annealing ambient on the electrical properties of Ta_2O_5 thin films prepared by plasma enhanced chemical vapor deposition. Thin Solid Films, 1994, 253, 435-439.	0.8	13
90	Formation of a large grain sized TiN layer using TiN_x , the epitaxial continuity at the Al/TiN interface, and its electromigration endurance in multilayered interconnection. Journal of Applied Physics, 1995, 78, 1719-1724.	1.1	13

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91	Improved electrical properties of tin-oxide films by using ultralow-pressure sputtering process. Thin Solid Films, 2009, 518, 1170-1173.	0.8	13
92	Atomic Layer Deposition of Ruthenium Nanoparticles Using a Low-Density Dielectric Film as Template Structure. Chemistry of Materials, 2009, 21, 4006-4011.	3.2	13
93	Capacitance and Interface Analysis of Transparent Analog Capacitor Using Indium Tin Oxide Electrodes and High-k Dielectrics. Journal of the Electrochemical Society, 2010, 157, G170.	1.3	13
94	The Anomalous Effect of Oxygen Ratio on the Mobility and Photobias Stability of Sputtered Zinc-Tin-Oxide Transistors. IEEE Transactions on Electron Devices, 2014, 61, 2071-2077.	1.6	13
95	Deposition and characterization of Pb TiO ₃ thin films on silicon wafers using metalorganic sources. Journal of Electronic Materials, 1993, 22, 707-716.	1.0	12
96	Comparison of ultrathin SiO ₂ films grown by thermal oxidation in an N ₂ O ambient with those in a 33% O ₂ /N ₂ ambient. Applied Physics Letters, 1994, 65, 2448-2450.	1.5	12
97	Homoepitaxial growth of 6H-SiC thin films by metal-organic chemical vapor deposition using bis-trimethylsilylmethane precursor. Journal of Crystal Growth, 2000, 210, 629-636.	0.7	12
98	Preparation and Characterization of Pb(Zr, Ti)O ₃ Thin Films by Metalorganic Chemical vapor Deposition Using a Solid Delivery System. Journal of Materials Research, 2000, 15, 1284-1290.	1.2	12
99	Effect of annealing on electrical properties of Pt ¹² -SiC contact. Solid-State Electronics, 2001, 45, 1565-1570.	0.8	12
100	Arsenic penetration behavior and electrical characteristics of As-doped n+ polycrystalline-silicon/high-k gate dielectric (HfO ₂ and Al ₂ O ₃) films on Si (100) substrate. Applied Physics Letters, 2003, 83, 1403-1405.	1.5	12
101	Study on the Step Coverage of Metallorganic Chemical Vapor Deposited TiO ₂ and SrTiO ₃ Thin Films. Journal of the Electrochemical Society, 2005, 152, C435.	1.3	12
102	Effect of stress and density on the electrical and physical properties of MgO protecting layer for alternating current-plasma display panels. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 1192-1196.	0.9	12
103	UV-O ₃ treatment effects on structural changes of low-k thin films. Microelectronic Engineering, 2007, 84, 2188-2191.	1.1	12
104	Analysis of the threshold switching mechanism of a Te-SbO selector device for crosspoint nonvolatile memory applications. Applied Physics Letters, 2017, 111, .	1.5	12
105	Deposition of Pb(Zr,Ti)O ₃ Thin Films by Metal-Organic Chemical Vapor Deposition Using ¹² -diketonate Precursors at Low Temperatures. Journal of the American Ceramic Society, 1995, 78, 329-336.	1.9	10
106	Effects of additives on the preferred orientation of Mn-Zn ferrite thin films deposited by ion beam sputtering. Applied Physics Letters, 1995, 66, 1282-1284.	1.5	10
107	Preparation of Homogeneous Polycrystalline CuInSe ₂ Thin Films by a Two-Step Chemical Vapor Transport Process. Journal of the Electrochemical Society, 1994, 141, 558-561.	1.3	9
108	Thickness dependence of the preferred orientation of Mn-Zn ferrite thin films deposited by ion beam sputtering. Journal of Applied Physics, 1995, 78, 418-422.	1.1	9

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109	Epitaxial growth of β -SiC thin films using bis-trimethylsilylmethane on Si(100) with a polycrystalline buffer layer. <i>Thin Solid Films</i> , 1996, 290-291, 181-185.	0.8	9
110	Electrical properties of (Pb,La)TiO ₃ thin films deposited by low pressure metal-organic chemical vapor deposition using solid delivery system. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1998, 16, 2591-2594.	0.9	9
111	Characterization of Undoped and Nitrogen-Doped 4H-SiC Thin Films by CVD from Bis(trimethylsilylmethane) Precursor. <i>Journal of the Electrochemical Society</i> , 2004, 151, G252.	1.3	9
112	Microstructural characterization of sputter-deposited Pt thin film electrode. <i>Journal of Materials Research</i> , 2004, 19, 460-468.	1.2	9
113	Improving the Performance of Tin Oxide Thin-Film Transistors by Using Ultralow Pressure Sputtering. <i>Journal of the Electrochemical Society</i> , 2010, 157, H425.	1.3	9
114	Effect of sputter power on the photobias stability of zinc-tin-oxide field-effect transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014, 32, 011202.	0.6	9
115	Improvement in Thermal Stability of Stacked Structures of Aluminum Nitride and Lanthanum Oxide Thin Films on Si Substrate. <i>Electrochemical and Solid-State Letters</i> , 2007, 10, G93.	2.2	8
116	Effects of Annealing Condition on Low-k a-SiOC:H Thin Films. <i>Electrochemical and Solid-State Letters</i> , 2007, 10, G11.	2.2	8
117	Homoepitaxial Growth of Vanadium-Doped Semi-insulating 4H-SiC Using Bis-trimethylsilylmethane and Bis-cyclopentadienylvanadium Precursors. <i>Journal of the Electrochemical Society</i> , 2008, 155, H11.	1.3	8
118	Effects of rapid thermal annealing on Al ₂ O ₃ /SiN reaction barrier layer/thermal-nitrided SiO ₂ stacking gate dielectrics on n-type 4H-SiC. <i>Applied Physics Letters</i> , 2010, 96, .	1.5	8
119	Unipolar resistive switching characteristics of pnictogen oxide films: Case study of Sb ₂ O ₅ . <i>Journal of Applied Physics</i> , 2012, 112, 104105.	1.1	8
120	Pb-Diffusion Barrier Layers for PbTiO ₃ Thin Films Deposited on Si Substrates by Metal Organic Chemical Vapor Deposition. <i>Journal of the American Ceramic Society</i> , 1995, 78, 337-341.	1.9	7
121	Layer sequence and silicide formation of a Co/(refractory metal) bilayer on (100)Si substrate. <i>Journal of Applied Physics</i> , 1995, 78, 6784-6790.	1.1	7
122	Electrical and microstructural properties of SrTiO ₃ thin films deposited by metalorganic chemical vapor deposition. <i>Integrated Ferroelectrics</i> , 1997, 14, 115-122.	0.3	7
123	Passivation layer effects on power durability of SAW duplexer. , 1999, , .		7
124	Morphological and structural characteristics of homoepitaxial 4H-SiC thin films by chemical vapor deposition using bis-trimethylsilylmethane precursor. <i>Thin Solid Films</i> , 2000, 377-378, 567-572.	0.8	7
125	Low Temperature 4H-SiC Epitaxial Growth on 4H-SiC (112̄ ₁ ,0) and (11̄ ₁ ,00) Faces by Organometallic Chemical Vapor Deposition. <i>Journal of the Electrochemical Society</i> , 2002, 149, G526.	1.3	7
126	Investigation of Ru/TiN Bottom Electrodes Prepared by Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 6635-6639.	0.8	7

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127	New DC Arc Discharge Synthesis Method for Carbon Nanotubes Using Xylene Ferrocene as Floating Catalyst. Japanese Journal of Applied Physics, 2007, 46, 1818-1820.	0.8	7
128	Dynamics of negative bias thermal stress-induced threshold voltage shifts in indium zinc oxide transistors: impact of the crystalline structure on the activation energy barrier. Journal Physics D: Applied Physics, 2014, 47, 165103.	1.3	7
129	Densification of silicon dioxide formed by plasma-enhanced atomic layer deposition on 4H-silicon carbide using argon post-deposition annealing. Ceramics International, 2018, 44, 13565-13571.	2.3	7
130	Effects of post-deposition annealing on sputtered SiO ₂ /4H-SiC metal-oxide-semiconductor. Solid-State Electronics, 2018, 139, 115-120.	0.8	7
131	Changes in structures and electrical conduction mechanisms of chemical vapor deposited Ta ₂ O ₅ thin films by annealing under O ₃ atmosphere with ultraviolet light radiation. Journal of Materials Research, 2004, 19, 1516-1523.	1.2	6
132	Heavily nitrogen-doped 4H-SiC homoepitaxial films grown on porous SiC substrates. Journal of Crystal Growth, 2007, 305, 83-87.	0.7	6
133	(Mn,Zn,Fe) _x O thin films showing ferrimagnetic property deposited by ion beam sputtering. Journal of Materials Research, 1995, 10, 274-279.	1.2	5
134	Analysis of stresses in Ru thin films prepared by chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 1381-1385.	0.9	5
135	Deep Submicron CMOS Technology Using Top-Edge Round STI and Dual Gate Oxide for Low Power 256 M-Bit Mobile DRAM. Japanese Journal of Applied Physics, 2003, 42, 1892-1896.	0.8	5
136	Pt-Doped Ru Films Prepared by CVD as Electrodes for DRAM Capacitors. Electrochemical and Solid-State Letters, 2005, 8, C12.	2.2	5
137	Effects of Thermally Oxidized-SiN Gate Oxide on 4H-SiC Substrate. Electrochemical and Solid-State Letters, 2007, 10, H327.	2.2	5
138	Impact of an Interfacial Layer on the Electrical Performance of p-Channel Tin Monoxide Field-Effect Transistors. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1700213.	1.2	5
139	Effects of oxygen partial pressure on the crystallographic structure of Mn-Zn ferrite thin films deposited by ion beam sputtering. Surface and Coatings Technology, 1994, 68-69, 279-284.	2.2	4
140	Optical Property of Pb(Zr, Ti)O ₃ Thin Films Deposited on Transparent Substrates by Atmospheric-Pressure Metal-Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1995, 34, 6112-6115.	0.8	4
141	Lowering of Leakage Current Density of (Ba,Sr)TiO ₃ Thin Films by Pulse Injection Deposition. Journal of the Electrochemical Society, 1998, 145, 3884-3889.	1.3	4
142	Characterization of 4H-SiC Homoepitaxial Films on Porous 4H-SiC from Bis(trimethylsilyl)methane Precursor. Journal of the Electrochemical Society, 2003, 150, G90.	1.3	4
143	Fabrication and Characterization of 4H-SiC Planar MESFET Using Ion- Implantation. Materials Science Forum, 2004, 457-460, 1181-1184.	0.3	4
144	The electrical and physical analysis of Pt gate/Al ₂ O ₃ /p-Si (100) with dual high-k gate oxide thickness for deep submicron complementary metal-oxide-semiconductor device with low power and high reliability. Journal of Electronic Materials, 2005, 34, 1104-1109.	1.0	4

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